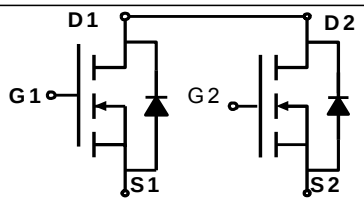
# N-Channel Enhancement Mode Power MOSFET TDM8205

## Description

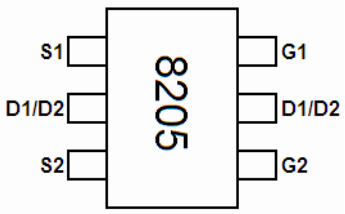
The TDM8205 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.




**Schematic diagram**

## General Features

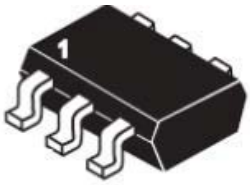
- $V_{DS}$ = 20V,$I_D$ = 4A
  $R_{DS(ON)}$ < 45mΩ @ $V_{GS}$=2.5V
  $R_{DS(ON)}$ < 30mΩ @ $V_{GS}$=4.5V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package




**Marking and pin Assignment**

## Application

- Battery protection
- Load switch
- Power management




**SOT23-6L top view**

## Package Marking And Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|---|---|---|---|---|---|
| 8205 | TDM8205 | SOT23-6L | Ø180mm | 8mm | 3000 units |

## Absolute Maximum Ratings (TA=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 20 | V |
| Gate-Source Voltage | $V_{GS}$ | ±10 | V |
| Drain Current-Continuous | $I_D$ | 4 | A |
| Drain Current-Pulsed (Note 1) | $I_{DM}$ | 25 | A |
| Maximum Power Dissipation | $P_D$ | 1.25 | W |
| Operating Junction and Storage Temperature Range | $T_J$,$T_{STG}$ | -55 To 150 | ℃ |

## Thermal Characteristic

| | | | |
|---|---|---|---|
| Thermal Resistance,Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 100 | ℃/W |

## Electrical Characteristics (TA=25℃unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V $I_D$=250μA | 20 | | | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=20V,$V_{GS}$=0V | | | 1 | μA |

| | | | | | | |
|---|---|---|---|---|---|---|
| Gate-Body Leakage Current | $I_{GSS}$ | $V_{GS}$=±10V,$V_{DS}$=0V | | | ±100 | nA |
| **On Characteristics (Note 3)** | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$=$V_{GS}$,$I_D$=250μA | 0.5 | | 1.2 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=4.5V, $I_D$=4A | | 22 | 30 | mΩ |
| | | $V_{GS}$=2.5V, $I_D$=3A | | 30 | 45 | mΩ |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$=5V,$I_D$=4A | | 10 | | S |
| **Dynamic Characteristics (Note4)** | | | | | | |
| Input Capacitance | $C_{lss}$ | $V_{DS}$=8V,$V_{GS}$=0V, F=1.0MHz | | 800 | | PF |
| Output Capacitance | $C_{oss}$ | | | 155 | | PF |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 125 | | PF |
| **Switching Characteristics (Note 4)** | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$=10V,$I_D$=1A $V_{GS}$=4V,$R_{GEN}$=10Ω | | 18 | | nS |
| Turn-on Rise Time | $t_r$ | | | 5 | | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 43 | | nS |
| Turn-Off Fall Time | $t_f$ | | | 20 | | nS |
| Total Gate Charge | $Q_g$ | $V_{DS}$=10V,$I_D$=4A, $V_{GS}$=4.5V | | 11 | | nC |
| Gate-Source Charge | $Q_{gs}$ | | | 2.3 | | nC |
| Gate-Drain Charge | $Q_{gd}$ | | | 2.5 | | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| Diode Forward Voltage (Note 3) | $V_{SD}$ | $V_{GS}$=0V,$I_S$=2A | | 0.8 | 1.2 | V |
| Diode Forward Current (Note 2) | $I_S$ | | | | 2 | A |

## Notes:

**1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
**2.** Surface Mounted on FR4 Board, t ≤ 10 sec.
**3.** Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
**4.** Guaranteed by design, not subject to production

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

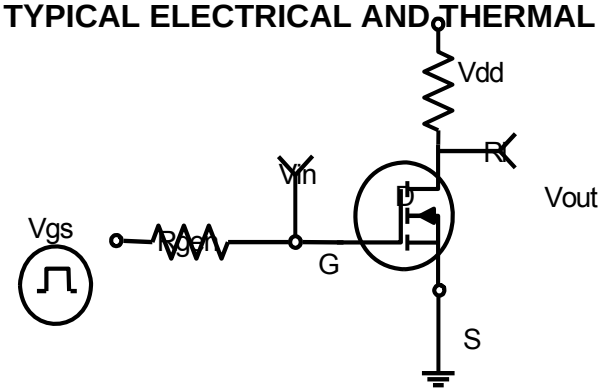



**Figure 1:Switching Test Circuit**

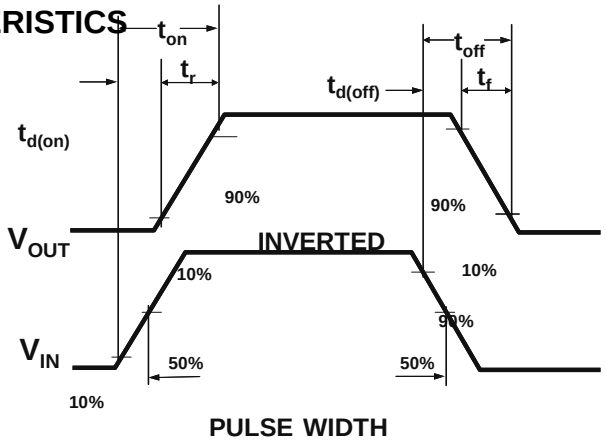



**Figure 2:Switching Waveforms**

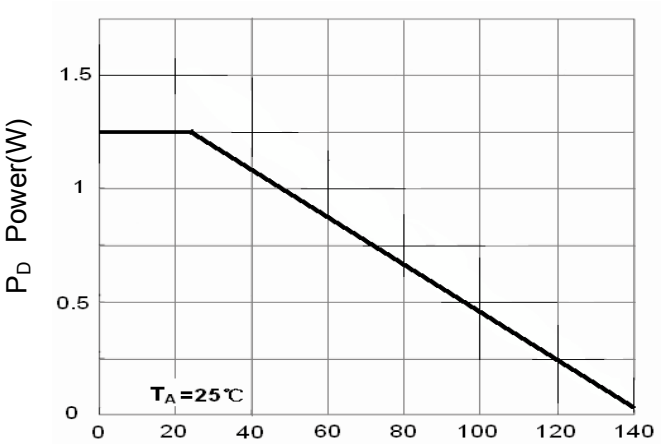



**Figure 3 Power Dissipation**

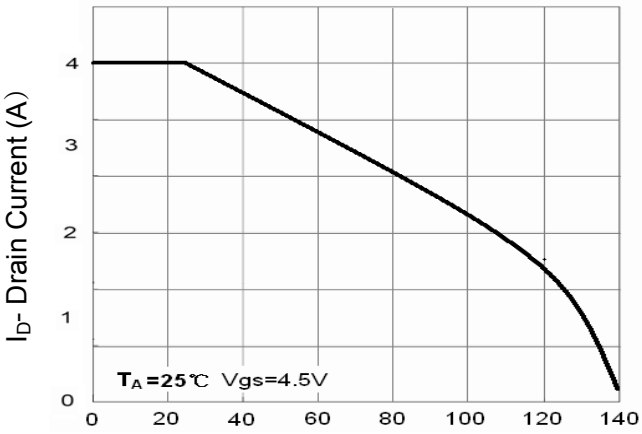



**Figure 4 Drain Current**

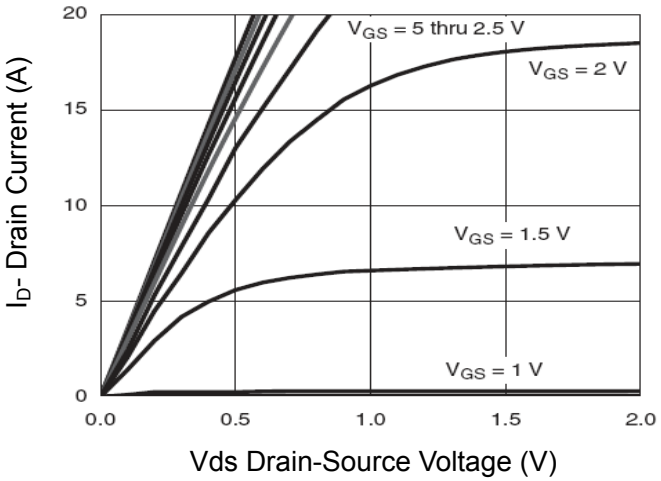



**Figure 5 Output CHARACTERISTICS**

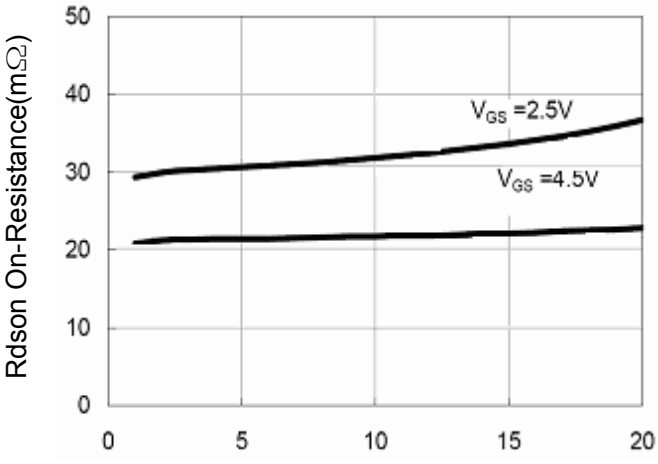



**Figure 6 Drain-Source On-Resistance**

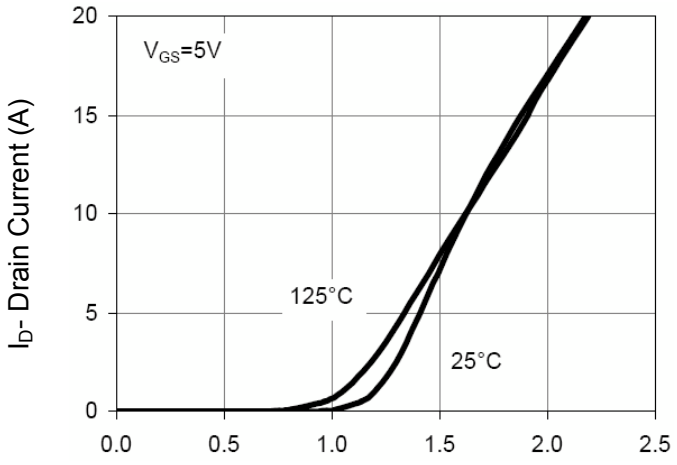



**Figure 7 Transfer Characteristics**

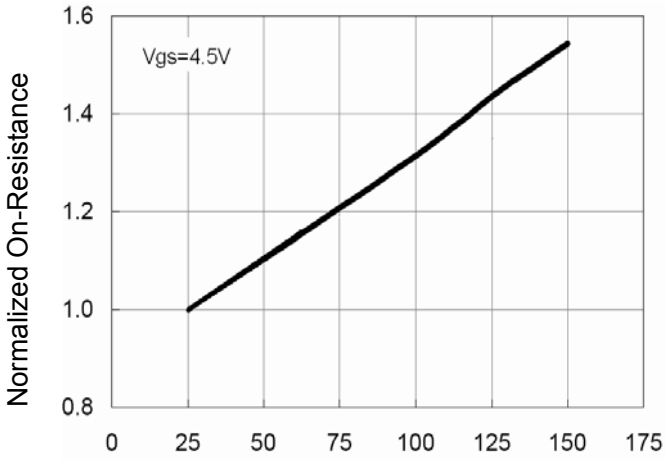



**Figure 8 Drain-Source On-Resistance**

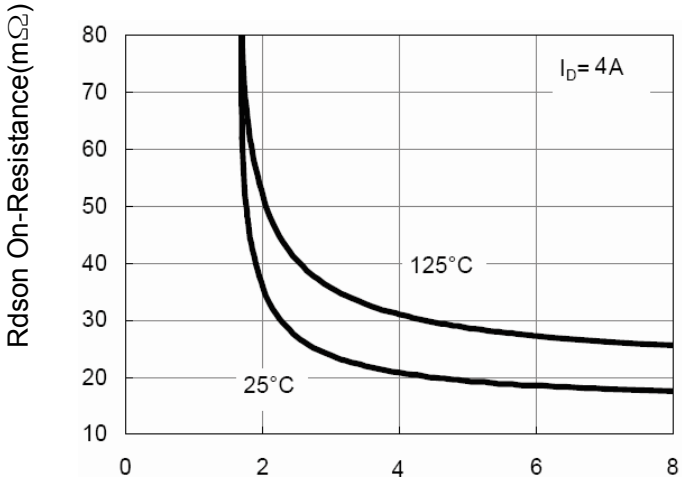



**Figure 9 Rdson vs Vgs**

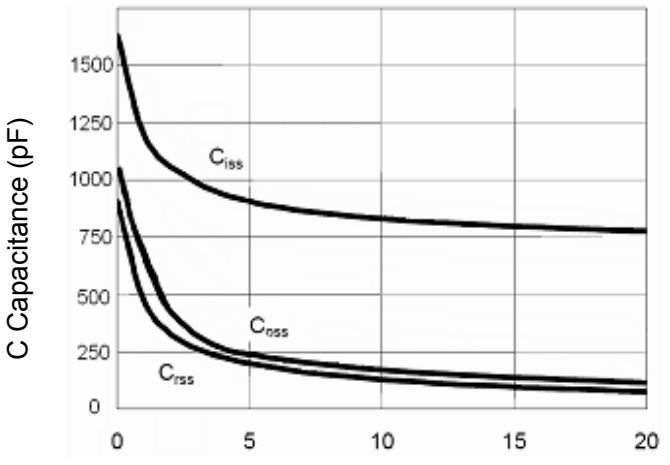



**Figure 10 Capacitance vs Vds**

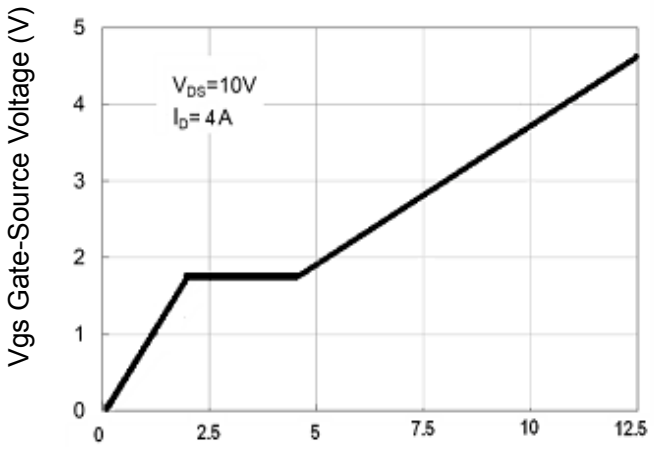



**Figure 11 Gate Charge**

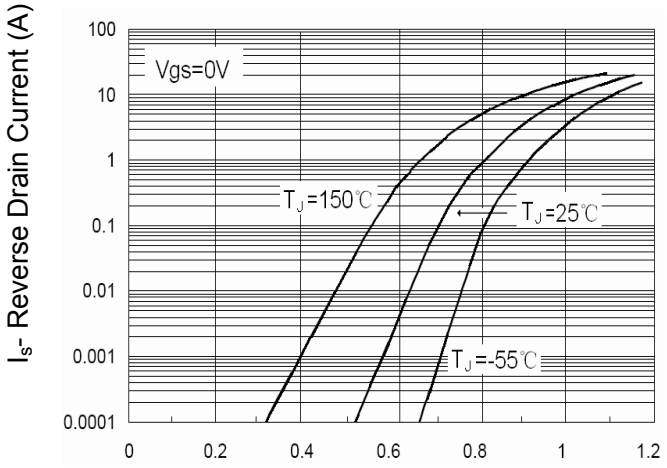
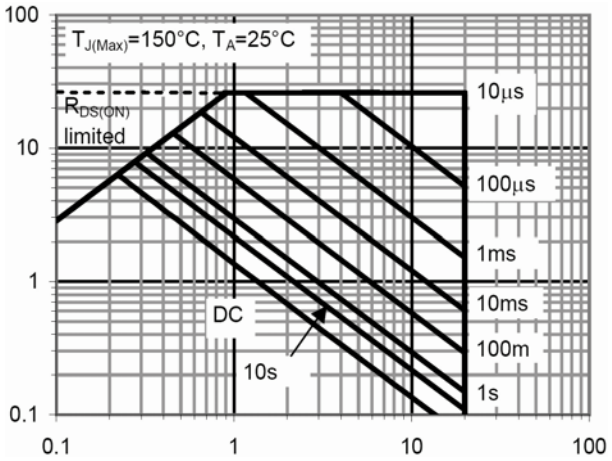
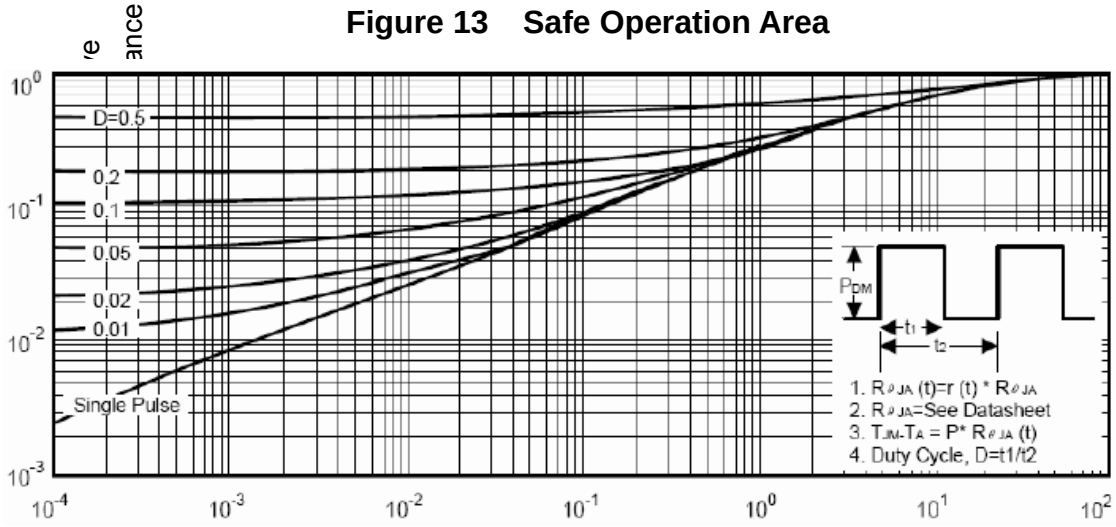



**Figure 12 Source- Drain Diode Forward**




Vds Drain-Source Voltage (V)

**Figure 13 Safe Operation Area**




Square Wave Pluse Duration(sec)

**Figure 14 Normalized Maximum Transient Thermal Impedance**

nformation herein are subject to change without notice.